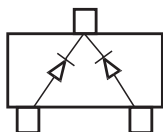


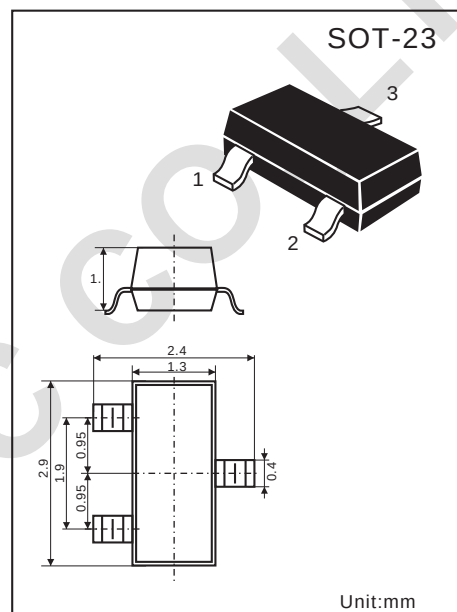
SOT-23 Plastic-Encapsulate DIODE

Features

- **Power dissipation**
 P_D : 150 mW ($T_{amb}=25^{\circ}\text{C}$)
- **Forward Current**
 I_F : 100 mA
- **Reverse Voltage**
 V_R : 80V
- **Operating and storage junction temperature range**
 T_j, T_{stg} : -55°C to $+150^{\circ}\text{C}$



Marking: B3



ELECTRICAL CHARACTERISTICS

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	80		V
Reverse Voltage leakage current	I_R	$V_R=80\text{V}$		0.5	μA
Forward Voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode Capacitance	C_{tot}	$V_R=0\text{V}$ $f=1\text{MHz}$		3	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1I_R$		4	nS

Typical Characteristics

